

GTL2018

8-bit LVTTTL to GTL transceiver

Rev. 01 — 15 February 2007

Product data sheet

1. General description

The GTL2018 is an octal translating transceiver designed for 3.3 V LVTTTL system interface with a GTL-/GTL/GTL+ bus.

The direction pin (DIR) allows the part to function as either a GTL-to-LVTTTL sampling receiver or as an LVTTTL-to-GTL interface.

The GTL2018 LVTTTL inputs (only) are tolerant up to 5.5 V, allowing direct access to TTL or 5 V CMOS inputs.

2. Features

- Operates as an octal GTL-/GTL/GTL+ sampling receiver or as an LVTTTL to GTL-/GTL/GTL+ driver
- 3.0 V to 3.6 V operation with 5 V tolerant LVTTTL input
- GTL input and output 3.6 V tolerant
- V_{ref} adjustable from 0.5 V to $0.5V_{CC}$
- Partial power-down permitted
- Latch-up protection exceeds 500 mA per JESD78
- ESD protection exceeds 2000 V HBM per JESD22-A114, 200 V MM per JESD22-A115, and 1000 V CDM per JESD22-CC101
- Package offered: TSSOP24

3. Quick reference data

Table 1. Quick reference data

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|---|-------------------------------|---|-----|-----|-----|------|
| C_i | input capacitance | control inputs; $V_I = 3.0\text{ V or }0\text{ V}$ | - | 2 | 2.5 | pF |
| C_{io} | input/output capacitance | A port; $V_O = 3.0\text{ V or }0\text{ V}$ | - | 4.6 | 6 | pF |
| | | B port; $V_O = V_{TT}$ or 0 V | - | 3.4 | 4.3 | pF |
| GTL; $V_{ref} = 0.8\text{ V}$; $V_{TT} = 1.2\text{ V}$ | | | | | | |
| t_{PLH} | LOW-to-HIGH propagation delay | An to Bn; see Figure 3 | - | 2.8 | 5 | ns |
| t_{PHL} | HIGH-to-LOW propagation delay | An to Bn; see Figure 3 | - | 3.4 | 7 | ns |
| t_{PLH} | LOW-to-HIGH propagation delay | Bn to An; see Figure 4 | - | 5.2 | 8 | ns |
| t_{PHL} | HIGH-to-LOW propagation delay | Bn to An; see Figure 4 | - | 4.9 | 7 | ns |

4. Ordering information

Table 2. Ordering information

$T_{amb} = -40\text{ }^{\circ}\text{C to } +85\text{ }^{\circ}\text{C}$.

| Type number | Topside mark | Package | | |
|-------------|--------------|---------|---|----------|
| | | Name | Description | Version |
| GTL2018PW | GTL2018PW | TSSOP24 | plastic thin shrink small outline package; 24 leads; body width 4.4 mm | SOT355-1 |

5. Functional diagram

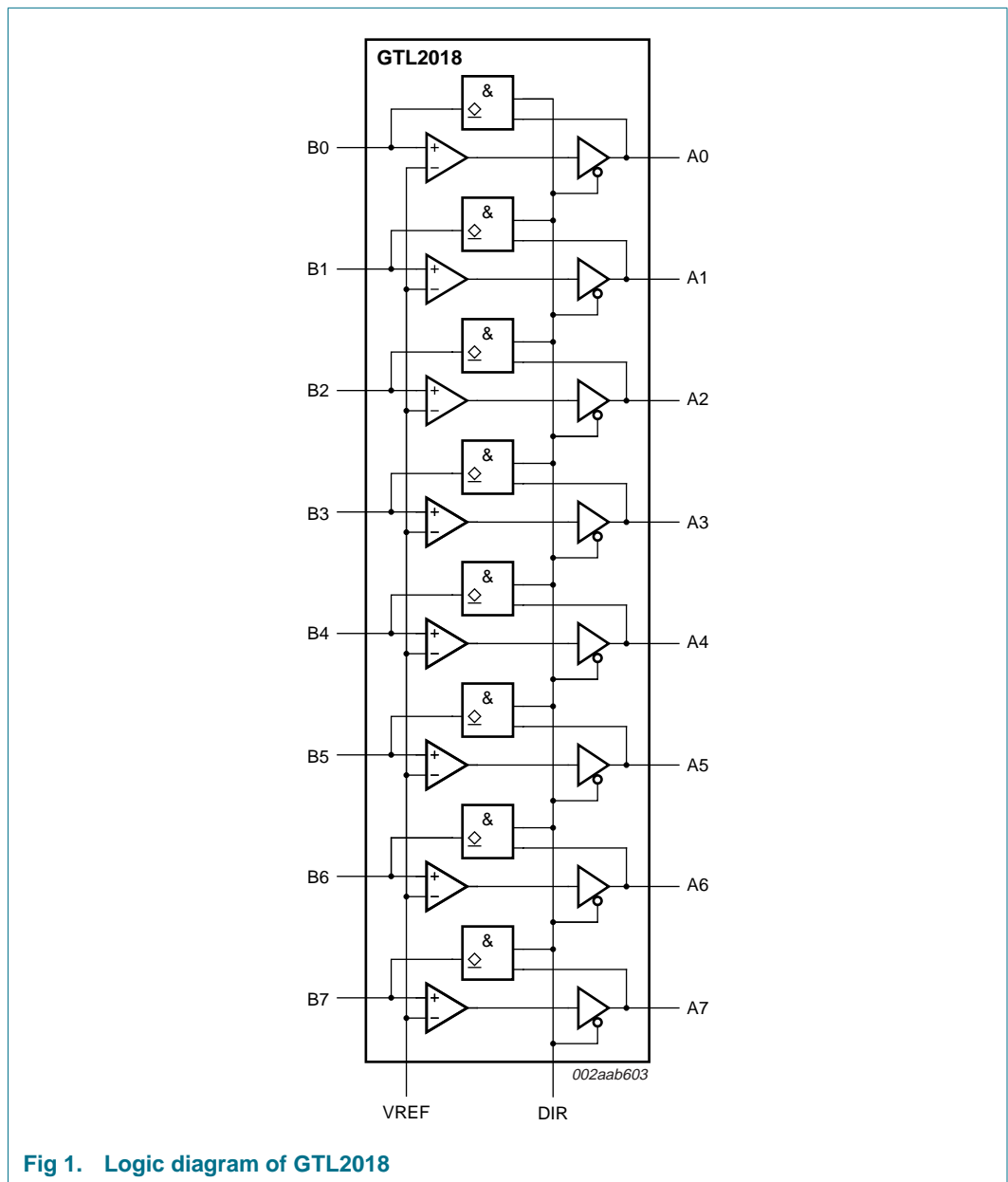


Fig 1. Logic diagram of GTL2018

6. Pinning information

6.1 Pinning

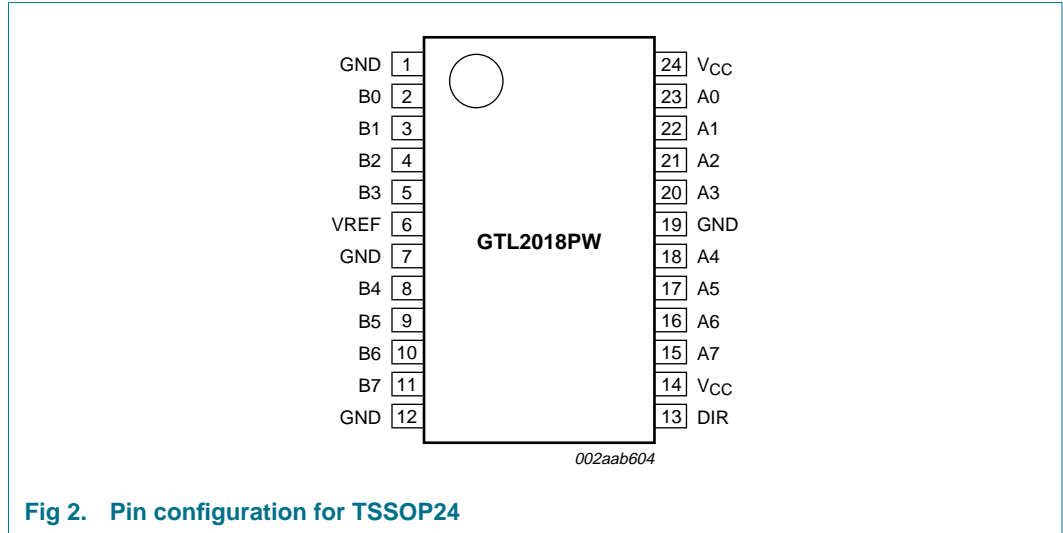


Fig 2. Pin configuration for TSSOP24

6.2 Pin description

Table 3. Pin description

| Symbol | Pin | Description |
|-----------------|--------------|--------------------------------------|
| GND | 1, 7, 12, 19 | ground (0 V) |
| B0 | 2 | data inputs/outputs (B side, GTL) |
| B1 | 3 | |
| B2 | 4 | |
| B3 | 5 | |
| B4 | 8 | |
| B5 | 9 | |
| B6 | 10 | |
| B7 | 11 | |
| VREF | 6 | GTL reference voltage |
| DIR | 13 | direction control input (LVTTTL) |
| V _{CC} | 14, 24 | positive supply voltage |
| A7 | 15 | data inputs/outputs (A side, LVTTTL) |
| A6 | 16 | |
| A5 | 17 | |
| A4 | 18 | |
| A3 | 20 | |
| A2 | 21 | |
| A1 | 22 | |
| A0 | 23 | |

7. Functional description

Refer to [Figure 1 “Logic diagram of GTL2018”](#).

7.1 Function table

Table 4. Function table

H = HIGH voltage level; L = LOW voltage level.

| Input | Input/output | |
|-------|--------------|----------|
| DIR | An (LVTTTL) | Bn (GTL) |
| H | input | Bn = An |
| L | An = Bn | input |

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Voltages are referenced to GND (ground = 0 V).

| Symbol | Parameter | Conditions | Min | Max | Unit |
|-----------|---------------------------|-------------------------------------|---------------------|------|------|
| V_{CC} | supply voltage | | -0.5 | 4.6 | V |
| I_{IK} | input clamping current | $V_I < 0$ V | - | -50 | mA |
| V_I | input voltage | A port | -0.5 ^[1] | 7.0 | V |
| | | B port | -0.5 ^[1] | 4.6 | V |
| I_{OK} | output clamping current | $V_O < 0$ V | - | -50 | mA |
| V_O | output voltage | output in OFF or HIGH state; A port | -0.5 ^[1] | 7.0 | V |
| | | output in OFF or HIGH state; B port | -0.5 ^[1] | 4.6 | V |
| I_{OL} | LOW-level output current | A port | ^[2] - | 32 | mA |
| | | B port | ^[2] - | 80 | mA |
| I_{OH} | HIGH-level output current | A port | ^[3] - | -32 | mA |
| T_{stg} | storage temperature | | ^[4] -60 | +150 | °C |

[1] The input and output negative voltage ratings may be exceeded if the input and output clamp current ratings are observed.

[2] Current into any output in the LOW state.

[3] Current into any output in the HIGH state.

[4] The performance capability of a high-performance integrated circuit in conjunction with its thermal environment can create junction temperatures which are detrimental to reliability. The maximum junction temperature of this integrated circuit should not exceed 150 °C.

9. Recommended operating conditions

Table 6. Recommended operating conditions^[1]

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|-----------|------------------------------------|------------------------------|-------------------|---------------------|-------------------|------|
| V_{CC} | supply voltage | | 3.0 | - | 3.6 | V |
| V_{TT} | termination voltage ^[2] | GTL- | 0.85 | 0.9 | 0.95 | V |
| | | GTL | 1.14 | 1.2 | 1.26 | V |
| | | GTL+ | 1.35 | 1.5 | 1.65 | V |
| V_{ref} | reference voltage | overall | 0.5 | $\frac{2}{3}V_{TT}$ | $0.5V_{CC}$ | V |
| | | GTL- | 0.5 | 0.6 | 0.63 | V |
| | | GTL | 0.76 | 0.8 | 0.84 | V |
| | | GTL+ | 0.87 | 1.0 | 1.10 | V |
| V_I | input voltage | B port | 0 | V_{TT} | 3.6 | V |
| | | except B port ^[3] | 0 | 3.3 | 5.5 | V |
| V_{IH} | HIGH-level input voltage | B port | $V_{ref} + 0.050$ | - | - | V |
| | | except B port | 2 | - | - | V |
| V_{IL} | LOW-level input voltage | B port | - | - | $V_{ref} - 0.050$ | V |
| | | except B port | - | - | 0.8 | V |
| I_{OH} | HIGH-level output current | A port | - | - | -16 | mA |
| I_{OL} | LOW-level output current | B port | - | - | 40 | mA |
| | | A port | - | - | 16 | mA |
| T_{amb} | ambient temperature | operating in free air | -40 | - | 85 | °C |

[1] Unused inputs must be held HIGH or LOW to prevent them from floating.

[2] V_{TT} maximum of 3.6 V with resistor sized to so I_{OL} maximum is not exceeded.

[3] A0 to A7 $V_{I(max)}$ is 3.6 V if configured as outputs (DIR = LOW).

10. Static characteristics

Table 7. Static characteristics

Recommended operating conditions; voltages are referenced to GND (ground = 0 V); $T_{amb} = -40\text{ }^{\circ}\text{C}$ to $+85\text{ }^{\circ}\text{C}$.

| Symbol | Parameter | Conditions | Min | Typ ^[1] | Max | Unit |
|---------------------------------|---------------------------|--|---------------------------|--------------------|------|------|
| V _{OH} | HIGH-level output voltage | A port; V _{CC} = 3.0 V to 3.6 V; I _{OH} = -100 μA | [2] V _{CC} - 0.2 | - | - | V |
| | | A port; V _{CC} = 3.0 V; I _{OH} = -16 mA | [2] 2.0 | - | - | V |
| V _{OL} | LOW-level output voltage | B port; V _{CC} = 3.0 V; I _{OL} = 40 mA | [2] - | 0.23 | 0.4 | V |
| | | A port; V _{CC} = 3.0 V; I _{OL} = 8 mA | [2] - | 0.28 | 0.4 | V |
| | | A port; V _{CC} = 3.0 V; I _{OL} = 12 mA | [2] - | 0.40 | 0.55 | V |
| | | A port; V _{CC} = 3.0 V; I _{OL} = 16 mA | [2] - | 0.55 | 0.8 | V |
| I _I | input current | control inputs; V _{CC} = 3.6 V; V _I = V _{CC} or GND | - | - | ±1 | μA |
| | | B port; V _{CC} = 3.6 V; V _I = V _{TT} or GND | - | - | ±1 | μA |
| | | A port; V _{CC} = 0 V or 3.6 V; V _I = 5.5 V | - | - | 10 | μA |
| | | A port; V _{CC} = 3.6 V; V _I = V _{CC} | - | - | ±1 | μA |
| | | A port; V _{CC} = 3.6 V; V _I = 0 V | - | - | -5 | μA |
| I _{OZ} | off-state output current | A port; V _{CC} = 0 V; V _I or V _O = 0 V to 3.6 V | - | - | ±100 | μA |
| I _{CC} | supply current | A port; V _{CC} = 3.6 V; V _I = V _{CC} or GND; I _O = 0 mA | - | 8 | 12 | mA |
| | | B port; V _{CC} = 3.6 V; V _I = V _{TT} or GND; I _O = 0 mA | - | 8 | 12 | mA |
| ΔI _{CC} ^[3] | additional supply current | per input; A port or control inputs; V _{CC} = 3.6 V; V _I = V _{CC} - 0.6 V | - | - | 500 | μA |
| C _i | input capacitance | control inputs; V _I = 3.0 V or 0 V | - | 2 | 2.5 | pF |
| C _{io} | input/output capacitance | A port; V _O = 3.0 V or 0 V | - | 4.6 | 6 | pF |
| | | B port; V _O = V _{TT} or 0 V | - | 3.4 | 4.3 | pF |

[1] All typical values are measured at V_{CC} = 3.3 V and T_{amb} = 25 °C.

[2] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[3] This is the increase in supply current for each input that is at the specified TTL voltage level rather than V_{CC} or GND.

11. Dynamic characteristics

Table 8. Dynamic characteristics

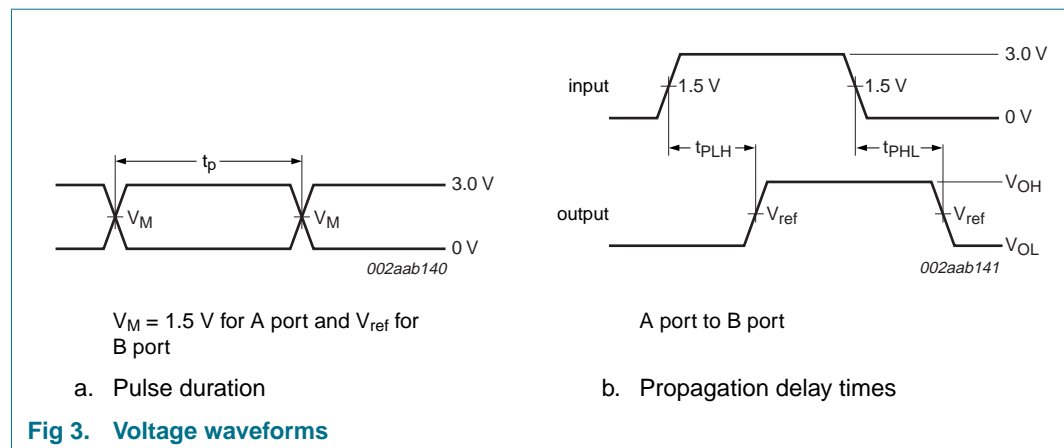
$V_{CC} = 3.3\text{ V} \pm 0.3\text{ V}$.

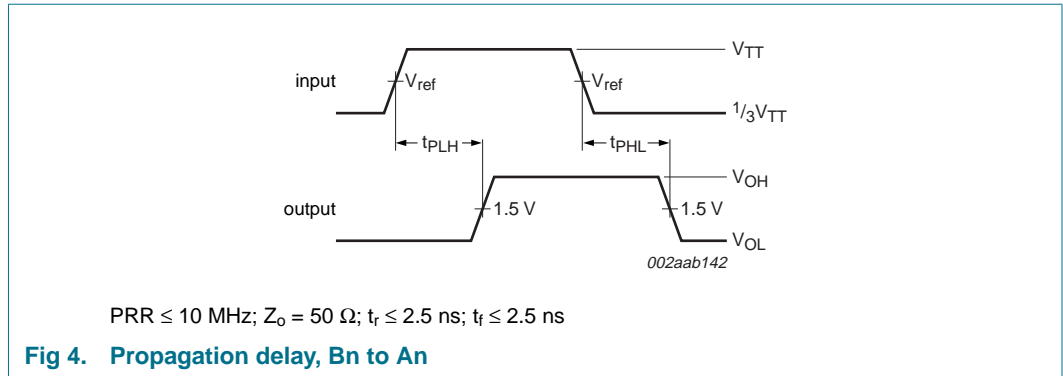
| Symbol | Parameter | Conditions | Min | Typ ^[1] | Max | Unit |
|--|-------------------------------|--|-----|--------------------|-----|------|
| GTL-; $V_{ref} = 0.6\text{ V}$; $V_{TT} = 0.9\text{ V}$ | | | | | | |
| t_{PLH} | LOW-to-HIGH propagation delay | An to Bn; see Figure 3 | - | 2.8 | 5 | ns |
| t_{PHL} | HIGH-to-LOW propagation delay | An to Bn; see Figure 3 | - | 3.3 | 7 | ns |
| t_{PLH} | LOW-to-HIGH propagation delay | Bn to An; see Figure 4 | - | 5.3 | 8 | ns |
| t_{PHL} | HIGH-to-LOW propagation delay | Bn to An; see Figure 4 | - | 5.2 | 8 | ns |
| GTL; $V_{ref} = 0.8\text{ V}$; $V_{TT} = 1.2\text{ V}$ | | | | | | |
| t_{PLH} | LOW-to-HIGH propagation delay | An to Bn; see Figure 3 | - | 2.8 | 5 | ns |
| t_{PHL} | HIGH-to-LOW propagation delay | An to Bn; see Figure 3 | - | 3.4 | 7 | ns |
| t_{PLH} | LOW-to-HIGH propagation delay | Bn to An; see Figure 4 | - | 5.2 | 8 | ns |
| t_{PHL} | HIGH-to-LOW propagation delay | Bn to An; see Figure 4 | - | 4.9 | 7 | ns |
| GTL+; $V_{ref} = 1.0\text{ V}$; $V_{TT} = 1.5\text{ V}$ | | | | | | |
| t_{PLH} | LOW-to-HIGH propagation delay | An to Bn; see Figure 3 | - | 2.8 | 5 | ns |
| t_{PHL} | HIGH-to-LOW propagation delay | An to Bn; see Figure 3 | - | 3.4 | 7 | ns |
| t_{PLH} | LOW-to-HIGH propagation delay | Bn to An; see Figure 4 | - | 5.1 | 8 | ns |
| t_{PHL} | HIGH-to-LOW propagation delay | Bn to An; see Figure 4 | - | 4.7 | 7 | ns |

[1] All typical values are at $V_{CC} = 3.3\text{ V}$ and $T_{amb} = 25\text{ }^\circ\text{C}$.

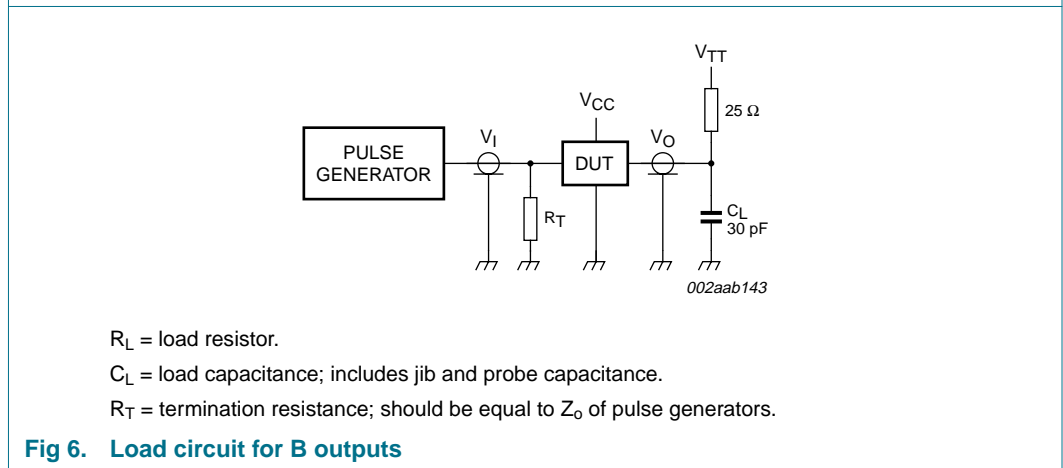
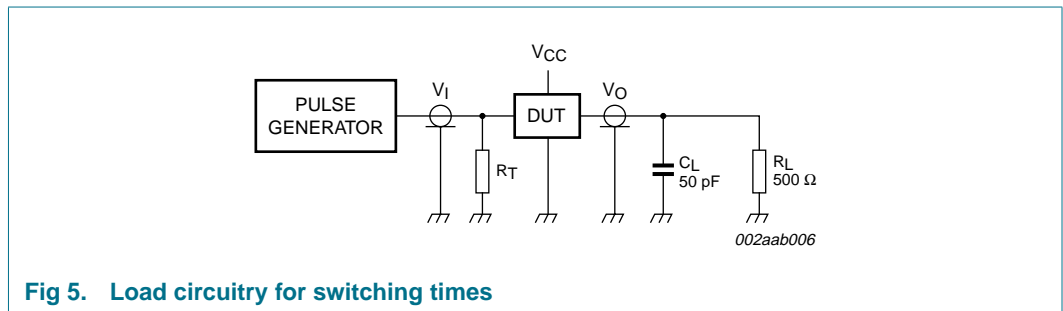
11.1 Waveforms

$V_M = 1.5\text{ V}$ at $V_{CC} \geq 3.0\text{ V}$; $V_M = 0.5V_{CC}$ at $V_{CC} \leq 2.7\text{ V}$ for A ports and control pins;
 $V_M = V_{ref}$ for B ports.





12. Test information



13. Package outline

TSSOP24: plastic thin shrink small outline package; 24 leads; body width 4.4 mm

SOT355-1

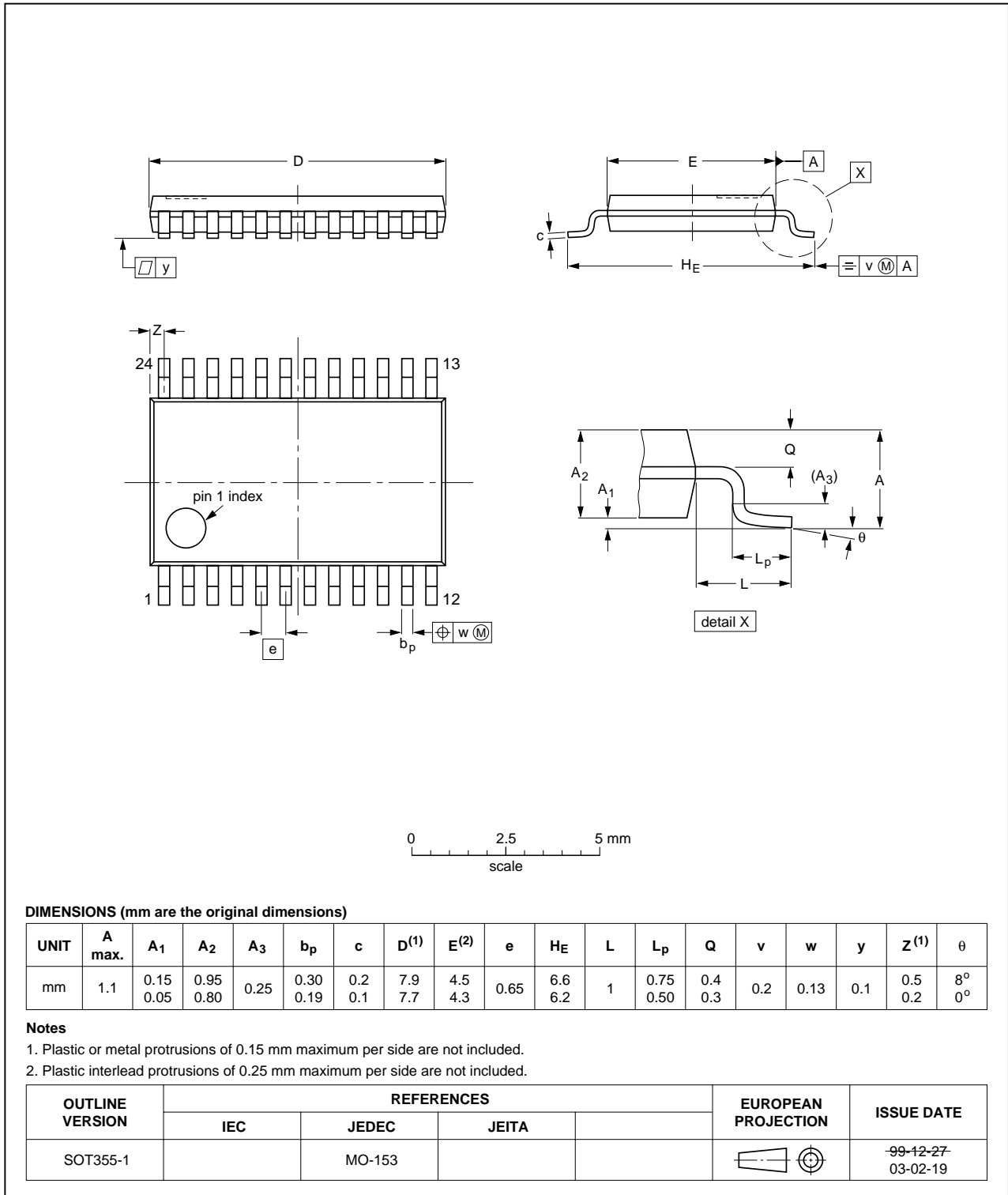


Fig 7. Package outline SOT355-1 (TSSOP24)

14. Soldering

This text provides a very brief insight into a complex technology. A more in-depth account of soldering ICs can be found in Application Note *AN10365 "Surface mount reflow soldering description"*.

14.1 Introduction to soldering

Soldering is one of the most common methods through which packages are attached to Printed Circuit Boards (PCBs), to form electrical circuits. The soldered joint provides both the mechanical and the electrical connection. There is no single soldering method that is ideal for all IC packages. Wave soldering is often preferred when through-hole and Surface Mount Devices (SMDs) are mixed on one printed wiring board; however, it is not suitable for fine pitch SMDs. Reflow soldering is ideal for the small pitches and high densities that come with increased miniaturization.

14.2 Wave and reflow soldering

Wave soldering is a joining technology in which the joints are made by solder coming from a standing wave of liquid solder. The wave soldering process is suitable for the following:

- Through-hole components
- Leaded or leadless SMDs, which are glued to the surface of the printed circuit board

Not all SMDs can be wave soldered. Packages with solder balls, and some leadless packages which have solder lands underneath the body, cannot be wave soldered. Also, leaded SMDs with leads having a pitch smaller than ~0.6 mm cannot be wave soldered, due to an increased probability of bridging.

The reflow soldering process involves applying solder paste to a board, followed by component placement and exposure to a temperature profile. Leaded packages, packages with solder balls, and leadless packages are all reflow solderable.

Key characteristics in both wave and reflow soldering are:

- Board specifications, including the board finish, solder masks and vias
- Package footprints, including solder thieves and orientation
- The moisture sensitivity level of the packages
- Package placement
- Inspection and repair
- Lead-free soldering versus PbSn soldering

14.3 Wave soldering

Key characteristics in wave soldering are:

- Process issues, such as application of adhesive and flux, clinching of leads, board transport, the solder wave parameters, and the time during which components are exposed to the wave
- Solder bath specifications, including temperature and impurities

14.4 Reflow soldering

Key characteristics in reflow soldering are:

- Lead-free versus SnPb soldering; note that a lead-free reflow process usually leads to higher minimum peak temperatures (see [Figure 8](#)) than a PbSn process, thus reducing the process window
- Solder paste printing issues including smearing, release, and adjusting the process window for a mix of large and small components on one board
- Reflow temperature profile; this profile includes preheat, reflow (in which the board is heated to the peak temperature) and cooling down. It is imperative that the peak temperature is high enough for the solder to make reliable solder joints (a solder paste characteristic). In addition, the peak temperature must be low enough that the packages and/or boards are not damaged. The peak temperature of the package depends on package thickness and volume and is classified in accordance with [Table 9](#) and [10](#)

Table 9. SnPb eutectic process (from J-STD-020C)

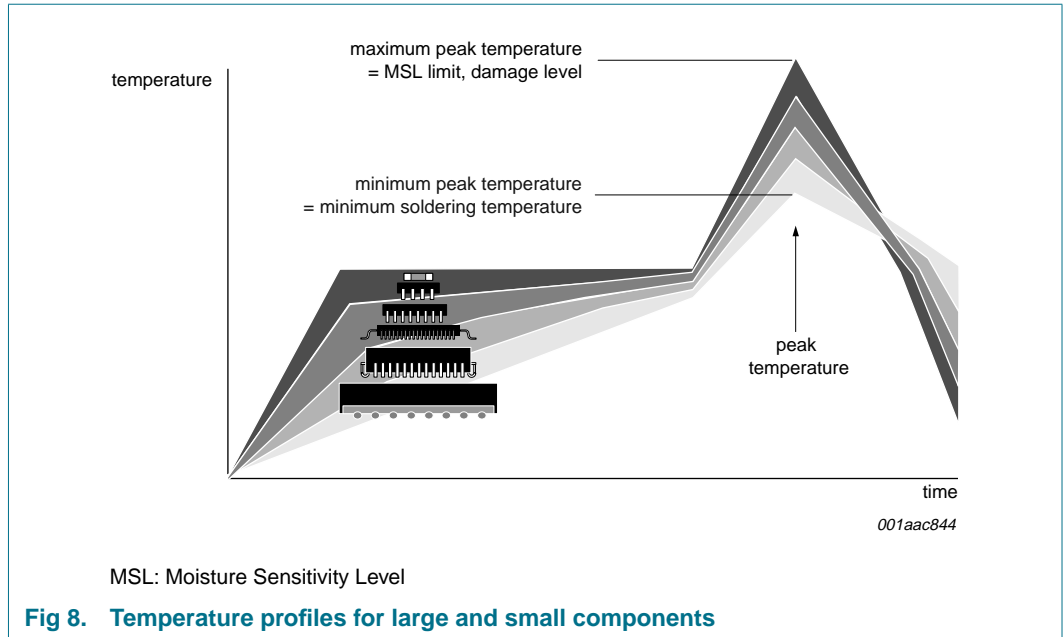
| Package thickness (mm) | Package reflow temperature (°C) | |
|------------------------|---------------------------------|-------|
| | Volume (mm ³) | |
| | < 350 | ≥ 350 |
| < 2.5 | 235 | 220 |
| ≥ 2.5 | 220 | 220 |

Table 10. Lead-free process (from J-STD-020C)

| Package thickness (mm) | Package reflow temperature (°C) | | |
|------------------------|---------------------------------|-------------|--------|
| | Volume (mm ³) | | |
| | < 350 | 350 to 2000 | > 2000 |
| < 1.6 | 260 | 260 | 260 |
| 1.6 to 2.5 | 260 | 250 | 245 |
| > 2.5 | 250 | 245 | 245 |

Moisture sensitivity precautions, as indicated on the packing, must be respected at all times.

Studies have shown that small packages reach higher temperatures during reflow soldering, see [Figure 8](#).



For further information on temperature profiles, refer to Application Note AN10365 “Surface mount reflow soldering description”.

15. Abbreviations

Table 11. Abbreviations

| Acronym | Description |
|---------|---|
| CDM | Charged Device Model |
| CMOS | Complementary Metal Oxide Semiconductor |
| DUT | Device Under Test |
| ESD | ElectroStatic Discharge |
| GTL | Gunning Transceiver Logic |
| HBM | Human Body Model |
| LVTTTL | Low Voltage Transistor-Transistor Logic |
| MM | Machine Model |
| PRR | Pulse Repetition Rate |
| TTL | Transistor-Transistor Logic |

16. Revision history

Table 12. Revision history

| Document ID | Release date | Data sheet status | Change notice | Supersedes |
|-------------|--------------|--------------------|---------------|------------|
| GTL2018_1 | 20070215 | Product data sheet | - | - |

17. Legal information

17.1 Data sheet status

| Document status ^{[1][2]} | Product status ^[3] | Definition |
|-----------------------------------|-------------------------------|---|
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19. Contents

1 General description 1

2 Features 1

3 Quick reference data 1

4 Ordering information 2

5 Functional diagram 2

6 Pinning information 3

6.1 Pinning 3

6.2 Pin description 3

7 Functional description 4

7.1 Function table 4

8 Limiting values 4

9 Recommended operating conditions 5

10 Static characteristics 6

11 Dynamic characteristics 7

11.1 Waveforms 7

12 Test information 8

13 Package outline 9

14 Soldering 10

14.1 Introduction to soldering 10

14.2 Wave and reflow soldering 10

14.3 Wave soldering 10

14.4 Reflow soldering 11

15 Abbreviations 12

16 Revision history 12

17 Legal information 13

17.1 Data sheet status 13

17.2 Definitions 13

17.3 Disclaimers 13

17.4 Trademarks 13

18 Contact information 13

19 Contents 14

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